

**Amendments to the Specification:**

Please amend paragraph [0008] of the originally filed specification as follows.

[0008] This and other objects are attained in accordance with one aspect of the invention directed to a method for depositing a material on a substrate wafer having the following method steps. Providing a substrate wafer, which has a growth area intended for a later material deposition. Before the deposition of a material on the growth area by means of MOVPE, applying ~~Applying~~ a thermal radiation absorption layer, which exhibits a good absorption of thermal radiation on the rear side of the substrate wafer, which faces away from the growth area. Heating the substrate wafer to the deposition temperature. Depositing a material onto the growth area of the substrate wafer by an MOVPE method.